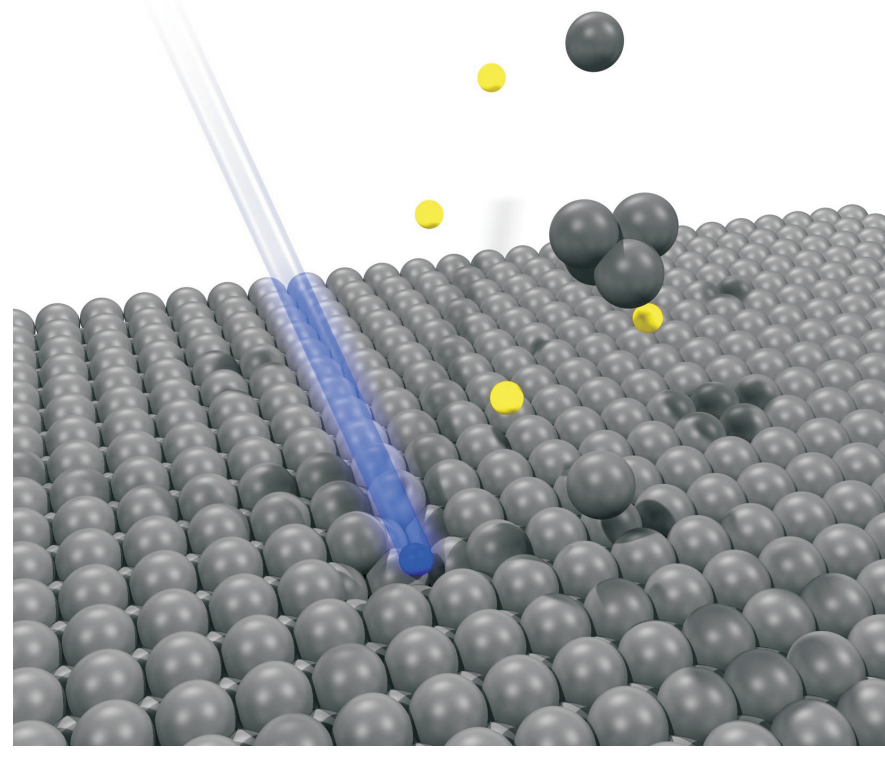


Track formation in  $\text{SrTiO}_3$ <sup>1</sup>Florian Meinerzhagen, <sup>1</sup>Hanna Bukowska, <sup>1</sup>Lars Breuer, <sup>1</sup>Andreas Wucher, <sup>2</sup>Daniel Severin, <sup>2</sup>Markus Bender, and <sup>1</sup>Marika Schleberger<sup>1</sup>Fakultät für Physik und CeNIDE, Universität Duisburg-Essen Germany<sup>2</sup>GSI Helmholzzentrum für Schwerionenforschung

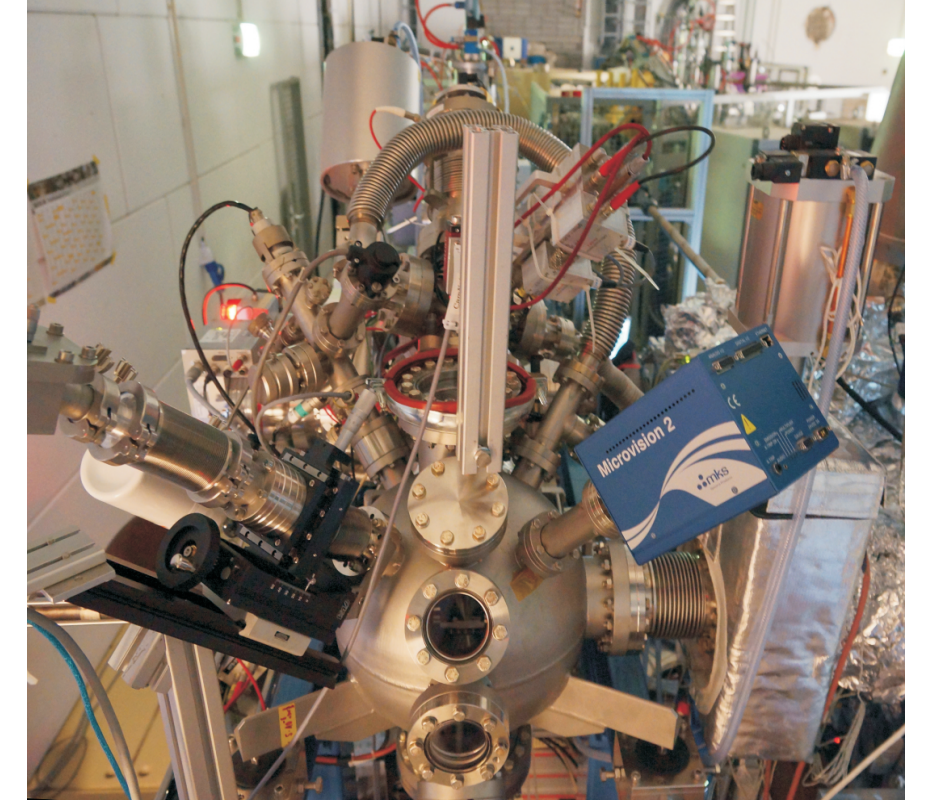
## Goals

- Investigation of energy dissipation processes during and after swift heavy ion (SHI) irradiation
- Analysis of ion induced structural modifications on the surface down to atomic level
- Determination of ionization probabilities under SHI irradiation
- Analysis of ionization processes to understand nano-structure formation in insulators



## Experiment

- Irradiation experiments at the M1 UNILAC beamline of GSI (Darmstadt, Germany)
- In-situ scanning probe microscopy set-up (Omicron) for characterization of the surface in ultra high vacuum
- multi-axial sample stage for irradiations with different angles of incidence and varying SHI energies
- Time-of-Flight-mass-spectrometer (TOF-MS) combined with VUV-laser for analysis of secondary ions and neutrals emitted during sputtering process

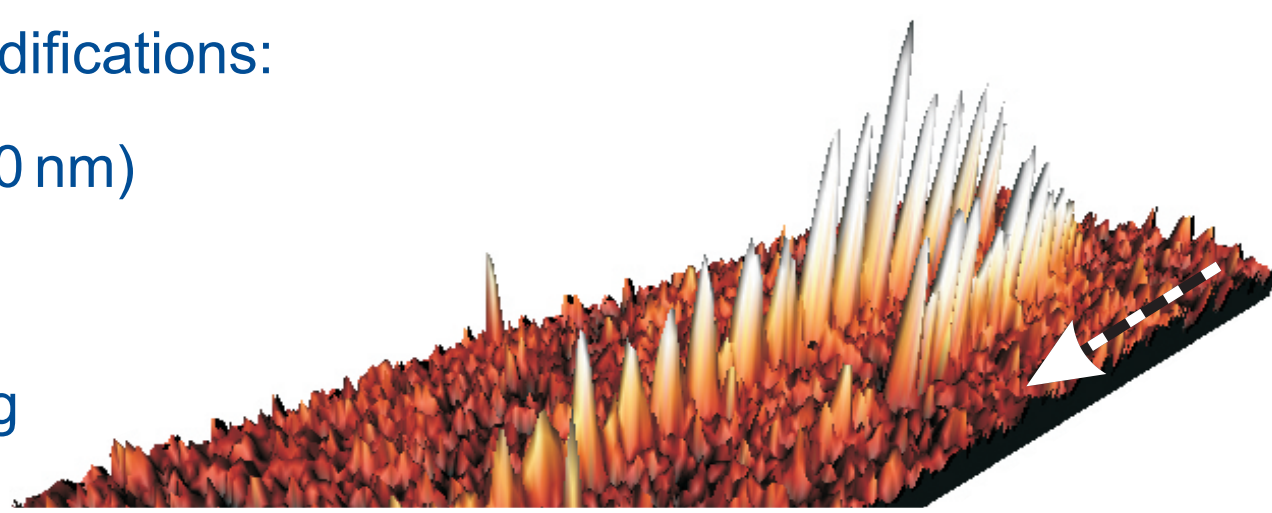
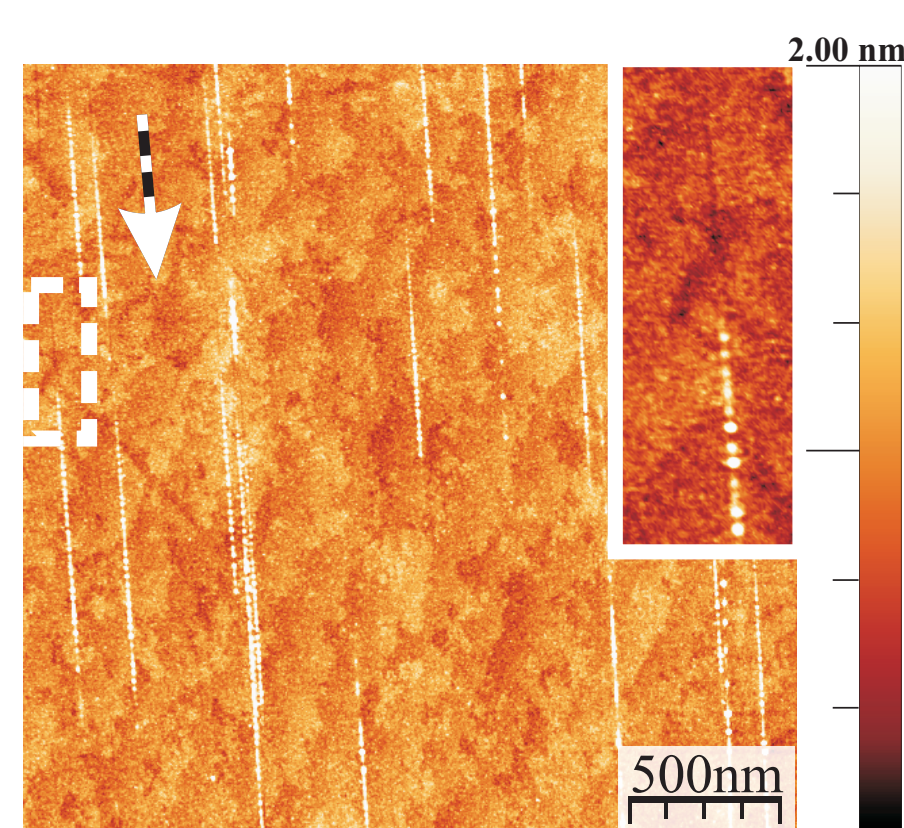


## Analysis of surface tracks via atomic force microscopy

## Irradiation of insulators

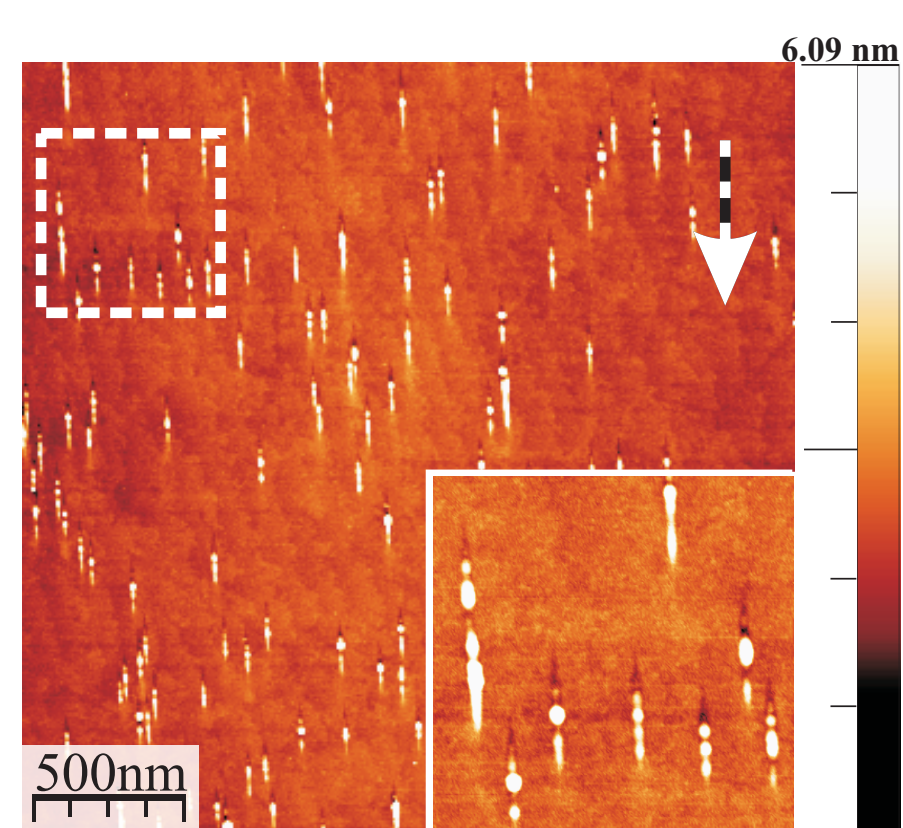
Irradiation of  $\text{SrTiO}_3$  with SHI leads to permanent modifications:

- 90° irradiation → hillocks (height  $\approx 5$  nm, diameter  $\approx 10$  nm)
- small angle ( $< 6^\circ$ ) → chains of hillocks [1]
  - novel feature - a rift - at the beginning of the chain of hillocks

 $\text{SrTiO}_3$ 

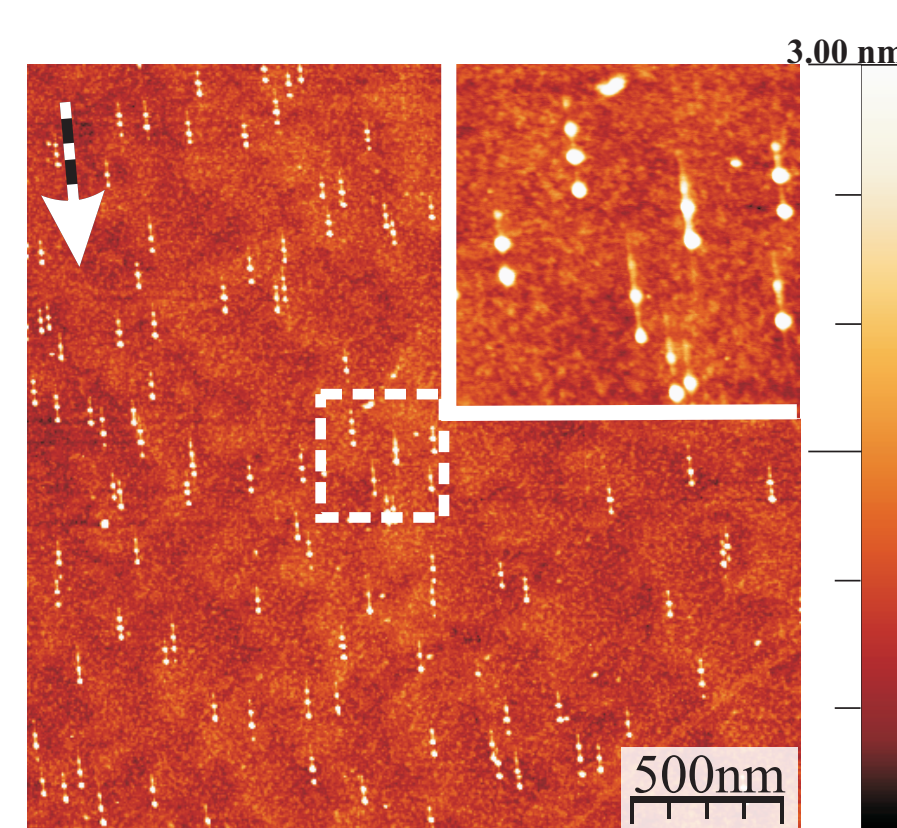
NC-AFM image of  $\text{SrTiO}_3$   
 $\Delta f = -22$  Hz,  $f_{\text{center}} = 181$  kHz  
 $^{136}\text{Xe}^{21+}$ ; 4.8 MeV/u;  $1.5^\circ$   
 Stopping power  $\approx 29$  keV/nm

Chain of hillocks:  
 length 690 nm  $\pm$  187 nm  
 Rift:  
 length 186 nm  $\pm$  50 nm  
 width 9 nm  $\pm$  2 nm  
 depth 0.3 nm  $\pm$  0.1 nm

 $\text{TiO}_2$ 

NC-AFM image of  $\text{SrTiO}_3$   
 $\Delta f = -22$  Hz,  $f_{\text{center}} = 181$  kHz  
 $^{238}\text{U}^{28+}$ ; 3.6 MeV/u;  $5.8^\circ$   
 Stopping power  $\approx 48$  keV/nm

Chain of hillocks:  
 length 109 nm  $\pm$  20 nm  
 Rift:  
 length 66 nm  $\pm$  13 nm  
 width 12 nm  $\pm$  4 nm  
 depth 0.7 nm  $\pm$  0.3 nm



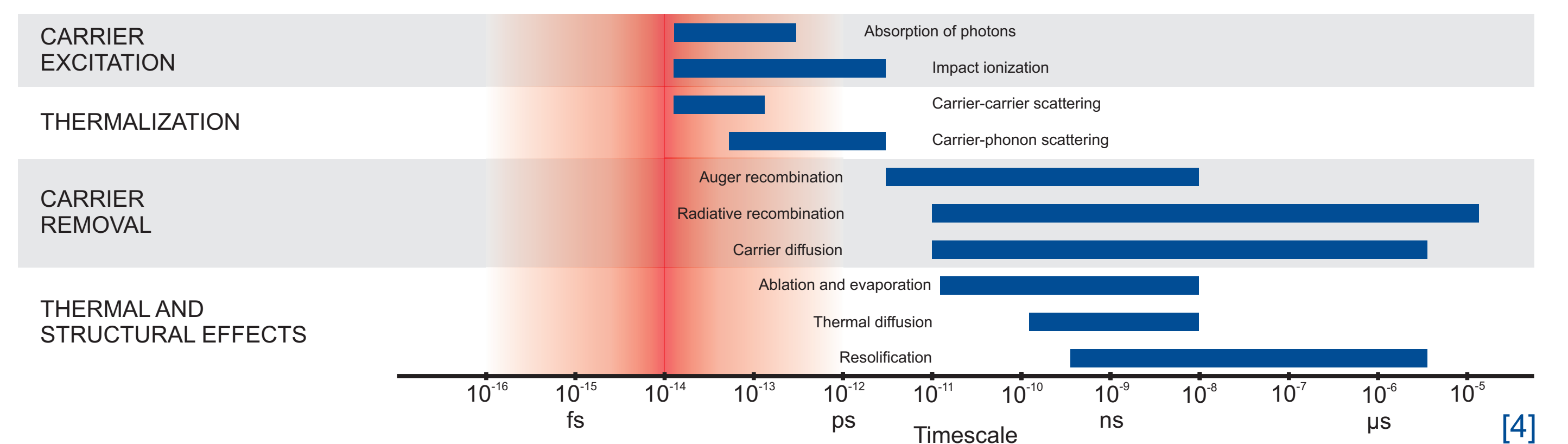
NC-AFM image of  $\text{TiO}_2$   
 $\Delta f = -23$  Hz,  $f_{\text{center}} = 181$  kHz  
 $^{136}\text{Xe}^{21+}$ ; 4.8 MeV/u;  $\approx 2^\circ$   
 Stopping power  $\approx 28$  keV/nm

No rifts observed

## Discussion

There are different approaches to explain SHI induced material modifications:

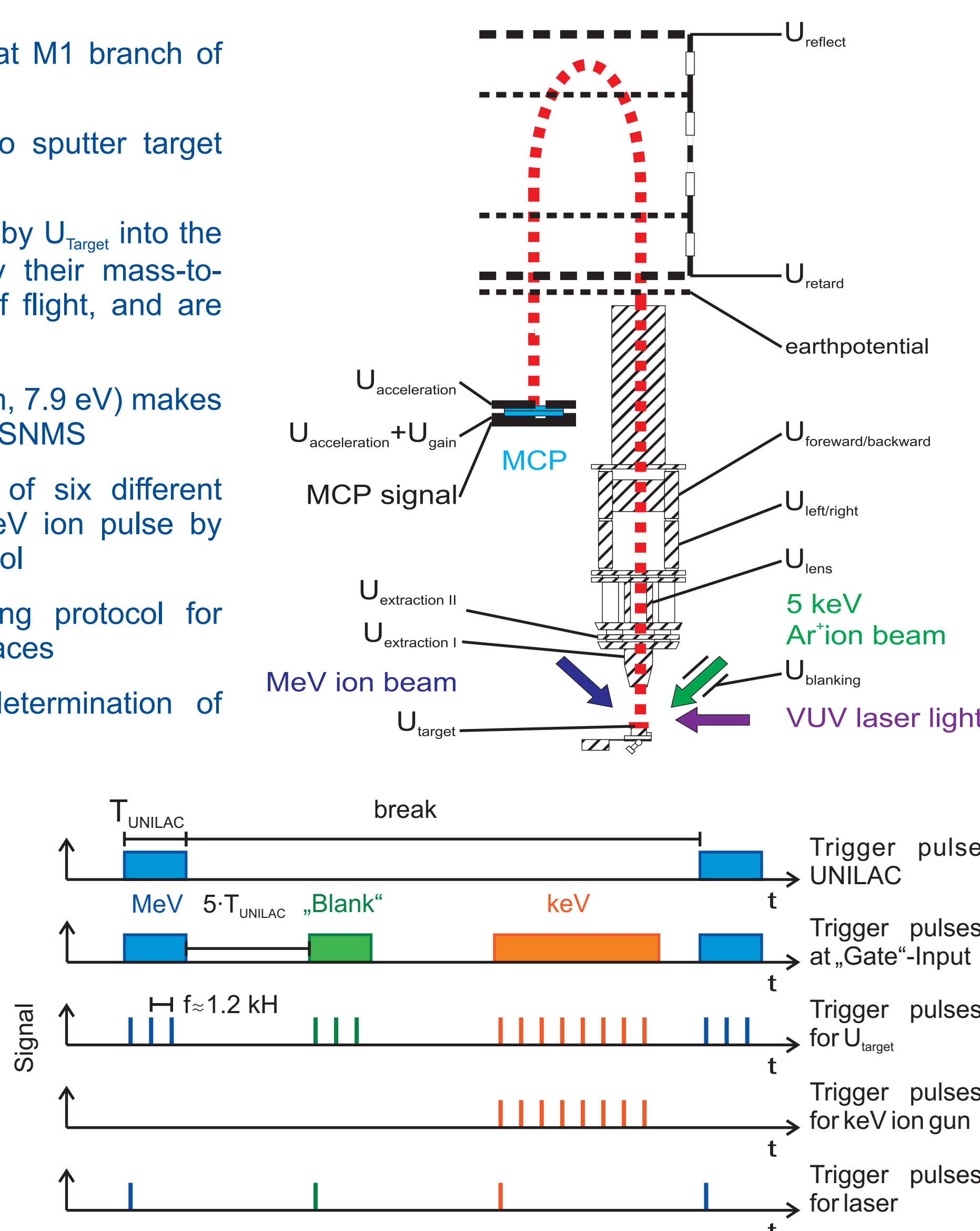
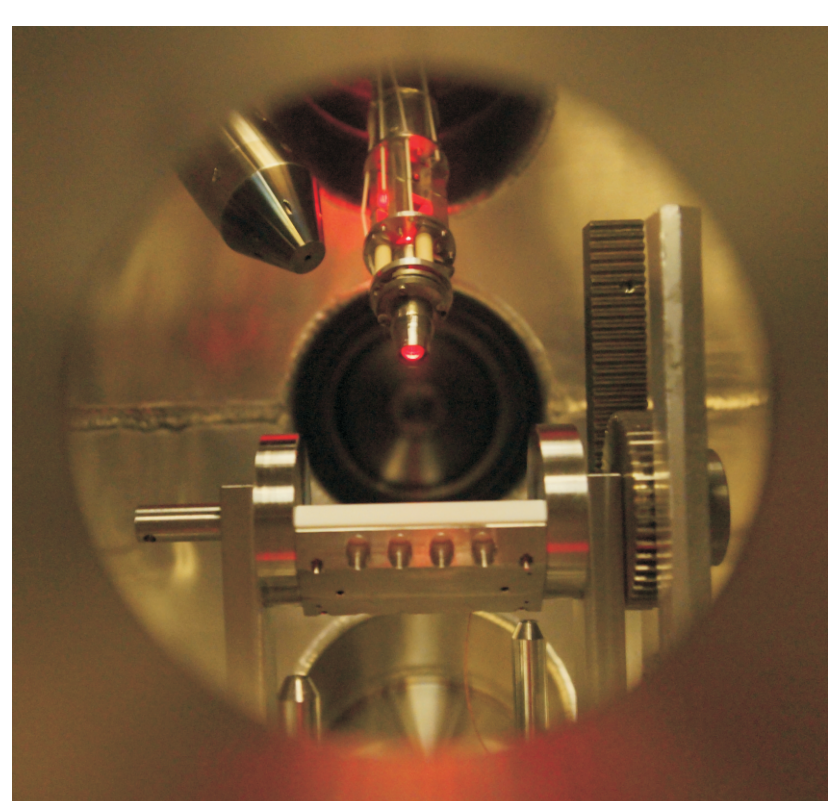
- Thermal-Spike-Model [2]**
  - Deposition of MeV/u ion energy in electronic sub-system of the target ( $\sim 10^{-16}$  -  $10^{-14}$  s)
  - Electron-phonon-coupling transfers energy to lattice subsystem ( $\sim 10^{-14}$  -  $10^{-11}$  s); leads e.g. to phase transitions (melting, sublimation, ...)
  - quantitative reproduction of energy threshold for track formation and radii [3]
  - model for explanation of chains of hillocks in combination with inhomogeneous electron density [5]
  - $\text{TiO}_2$  and  $\text{SrTiO}_3$  have nearly same melting and boiling temperatures ( $T_{\text{m,b,TiO}_2} = 1855^\circ\text{C}/2972^\circ\text{C}$ ,  $T_{\text{m,b,SrTiO}_3} = 2040^\circ\text{C}/3000^\circ\text{C}$ ,  $T_{\text{m,b,SrO}} = 2460^\circ\text{C}/3200^\circ\text{C}$ )
  - no sign for a thermal decomposition process as in the case of SiC [6] because one found neutral particles of all species in SNMS-spectra
- Coulomb-Explosion-Model [7]**
  - Ionization of atoms along the trajectory of MeV/u ion
  - Repulsion of charged target ions by Coulomb force
  - Possible particle emission of ionized particle [8]
    - Ionization probability of Sr in  $\text{SrTiO}_3$  should be higher and lead to higher sputter yield of  $\text{SrTiO}_3$  in comparison to  $\text{TiO}_2$ , which would explain the distinct rift formation (→ use a TOF-MS)
    - $\text{SrTiO}_3$  particles eject only as neutral clusters



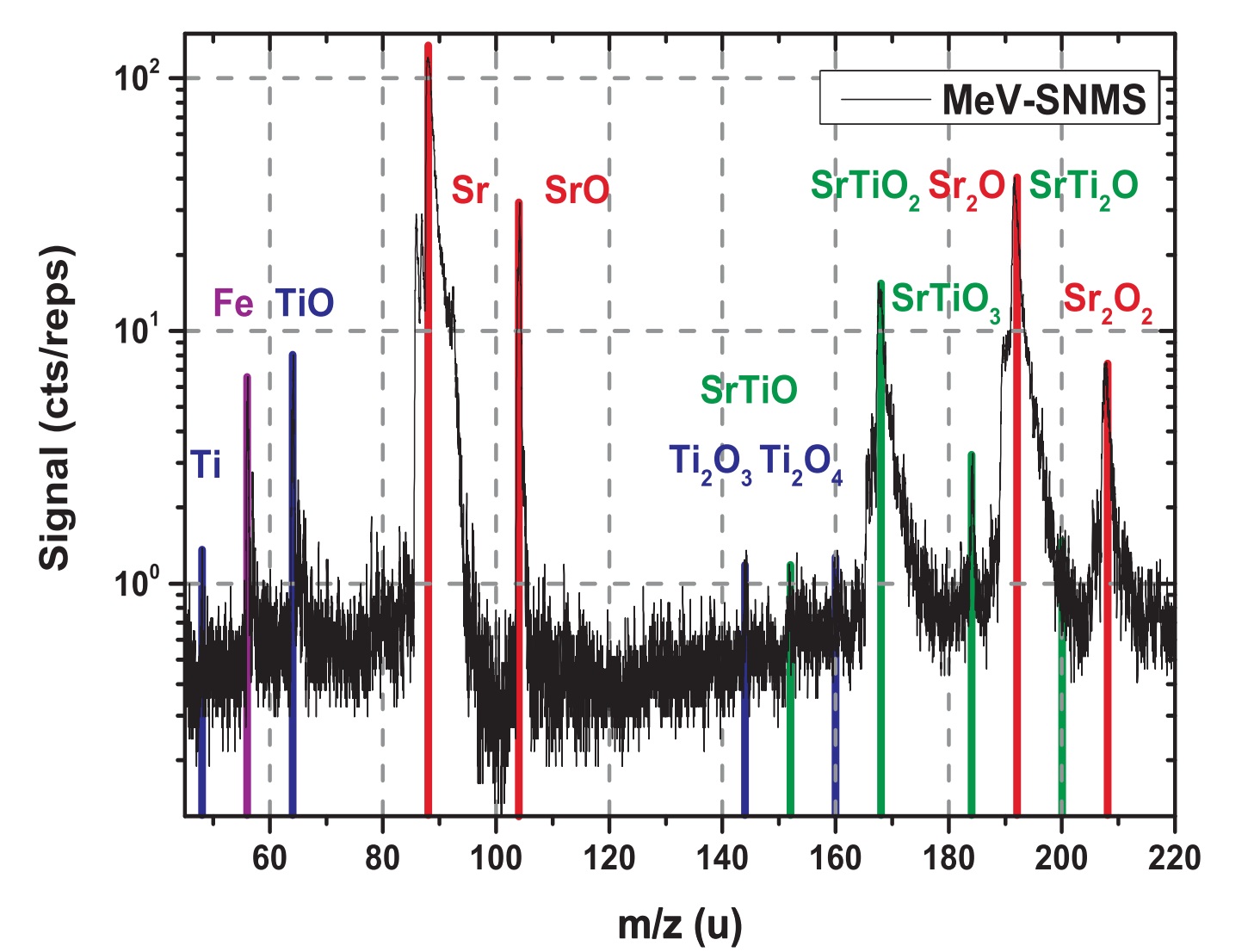
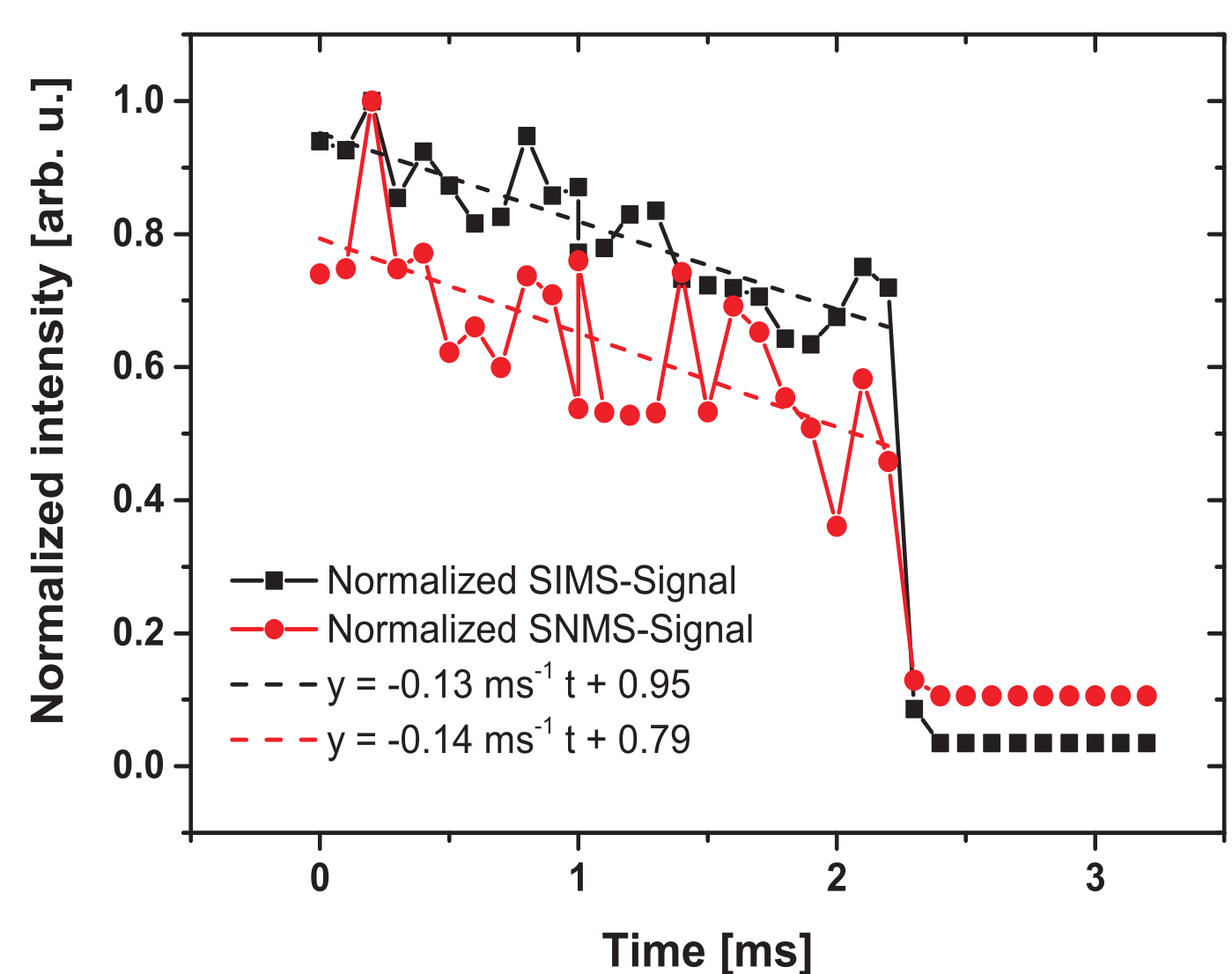
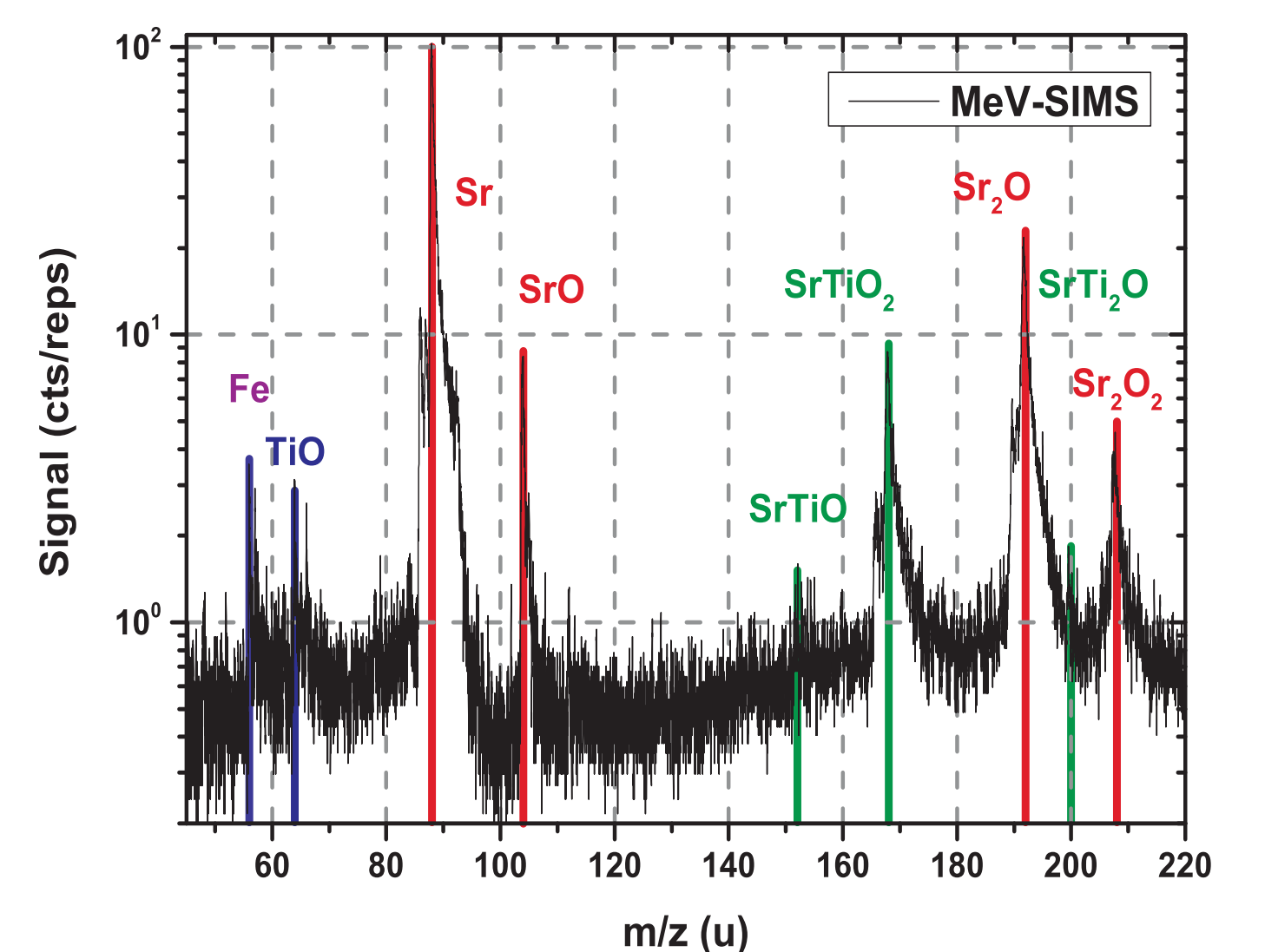
## Analysis of sputtered secondary particles

## New TOF-MS set-up

- New reflectron-based TOF-MS at M1 branch of UNILAC beamline in 2014
- MeV/u or keV ions are used to sputter target materials
- Secondary ions are accelerated by  $U_{\text{Target}}$  into the spectrometer, are separated by their mass-to-charge ratio during their time of flight, and are detected at a MCP → SIMS
- Laser post-ionization ( $\lambda = 157$  nm, 7.9 eV) makes secondary neutrals accessible → SNMS
- Quasi-simultaneous acquisition of six different spectra during one UNILAC MeV ion pulse by newly designed measuring protocol
- Interleaved keV sputter cleaning protocol for measurements of pure metal surfaces
- Pulse mapping protocol for determination of MeV/u ion pulse form

Mass spectra of  $\text{SrTiO}_3$ SIMS- (upper panel on the right hand side) and SNMS-signal (lower panel on the right hand side) of  $\text{SrTiO}_3$  irradiated with  $^{197}\text{Au}^{26+}$  4.8 MeV/u (stopping power  $\approx 28$  keV/nm)

- Sr and its oxides dominate both spectra
- No  $\text{SrTiO}_3$ -peak visible in SIMS
- Ti and its oxides better detectable in SNMS
- Possible mechanisms for ionisation by  $\text{Sr}^+$  cationization
- No influence of heating caused by MeV/u ion irradiation is observed for the signal (here  $\text{Sr}^+$ ) during irradiation (see normalized intensities of  $\text{Sr}^+$ -Peak during pulse mapping)



## References

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 [3] M. Toulemonde, C. Dufour, E. Paumier, Phys. Rev. B 46 (1992)  
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